

Appl. No. 10/723,456 Amdt. Dated Oct. 1, 2004 Reply to Office Action of July 1, 2004 Replacement Sheet

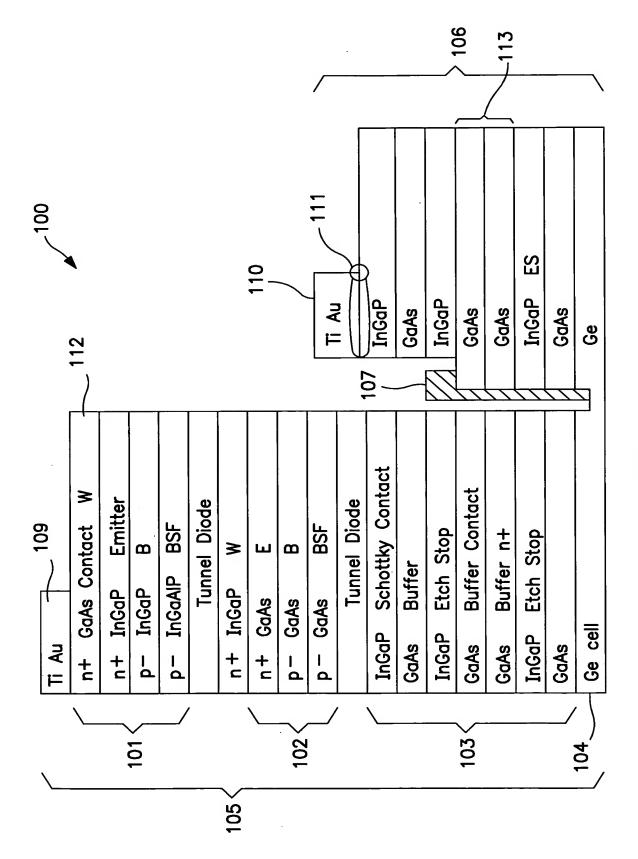


FIG.

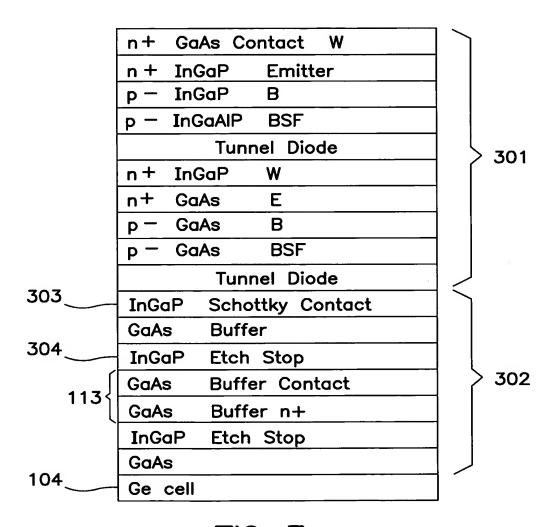


FIG. 3

	_ 100
n+Ga As Contact	
n + InGaP	
p - InGaP	
p — InGaAlP	
Tunnel Diode	
n+ InGaP	
n + GaAs	
p - GaAs	
p – GaAs	
Tunnel Diode	
InGaP Schottky	Contact 403
GaAs Buffer	
InGaP Etch Sto	рр
GaAs Buffer C	contact 113
GaAs Buffer n	
InGaP Etch Sto	op ·
GaAs	
Ge cell	

FIG. 4

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													104				
	-						501	502		/ InGap	GaAs	InGaP	GaAs	GaAs	InGaP ES	GaAs	Ge
n+ GaAs Contact W	n + InGaP Emitter	p - InGaP B	p - InGaAIP BSF	Tunnel Diode	n + InGaP W	n + GaAs E	p - GaAs B	p - GaAs BSF	Tunnel Diode	InGaP Schottky Contact	GaAs Buffer	InGaP Etch Stop	GaAs Buffer Contact	GaAs Buffer n+	InGaP Etch Stop	GaAs	Ge cell

FIG. 5